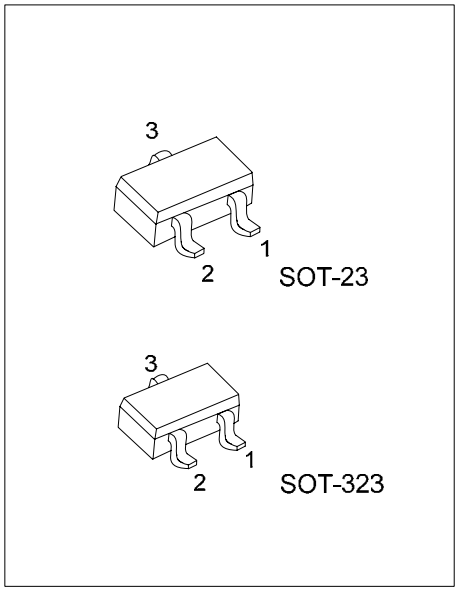
2SK2751

N-CHANNEL JFET

N-CHANNEL JUNCTION FET



*Pb-free plating product number:2SK2751L

■ FEATURES

* Low noise-figure (NF).
* High gate to drain voltage V_{GDO}.

■ APPLICATIONS

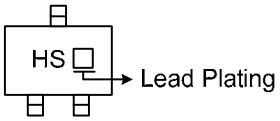
* For impedance conversion in low frequency.
* For pyroelectric sensor.

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SK2751-AE3-R	2SK2751L-AE3-R	SOT-23	D	S	G	Tape Reel
2SK2751-AL3-R	2SK2751L-AL3-R	SOT-323	D	S	G	Tape Reel

2SK2751L-AE3-R (1)Packing Type (2)Package Type (3)Lead Plating	(1) R: Tape Reel (2) AE3: SOT-23, AL3: SOT-323 (3) L: Lead Free Plating, Blank: Pb/Sn

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

PARAMETER	SYMBOL	RATINGS	UNIT
Gate-Drain Voltage	V_{GDS}	-40	V
Drain Current	I_D	10	mA
Gate Current	I_G	2	mA
Allowable Power Dissipation	P_D	200	mW
Channel Temperature	T_{CH}	+150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

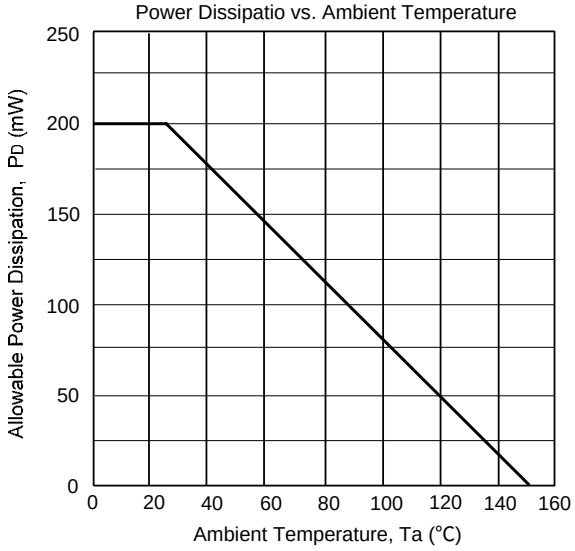
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25±3℃, unless otherwise specified)

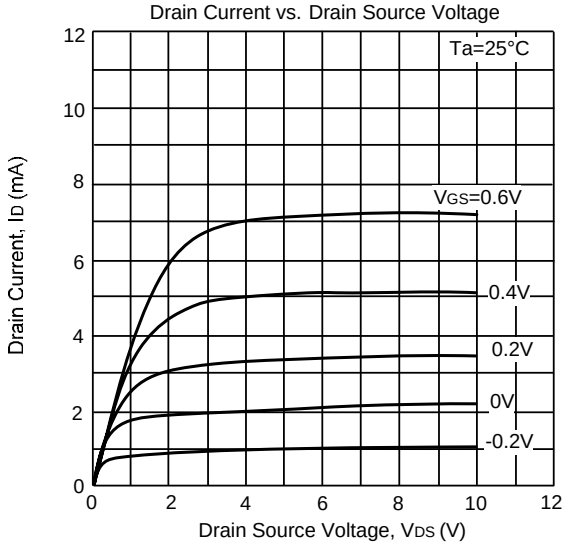
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate-Drain Voltage	V_{GDS}	I_G=-100μA, V_{DS}=0	-40			V
Gate-Source Cut-Off Voltage	V_{GSC}	V_{DS}=10V, I_D=1μA			-3.5	V
Drain-Source Cut-Off Current	I_{DSS}	V_{DS}=10V, V_{GS}=0	1.4		4.7	mA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=-20V, V_{DS}=0			-1	nA
Forward Transfer Admittance	$\lvert Y_{fs} \rvert$	V_{DS}=10V, V_{GS}=0, f=1kHz	2.5			mS
Input Capacitance (Common Source)	C_{ISS}	V_{DS}=10V, V_{GS}=0, f=1MHz		5		pF
Output Capacitance (Common Source)	C_{OSS}			1		pF
Reverse Transfer Capacitance (Common Source)	C_{RSS}			1		pF

■ TYPICAL CHARACTERISTICS

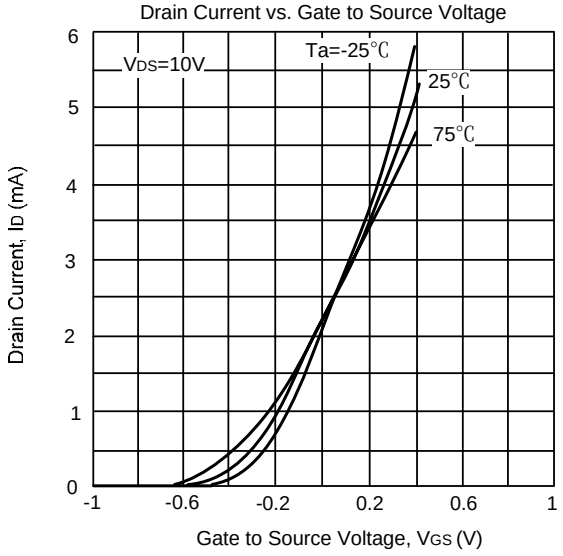
Power Dissipatio vs. Ambient Temperature



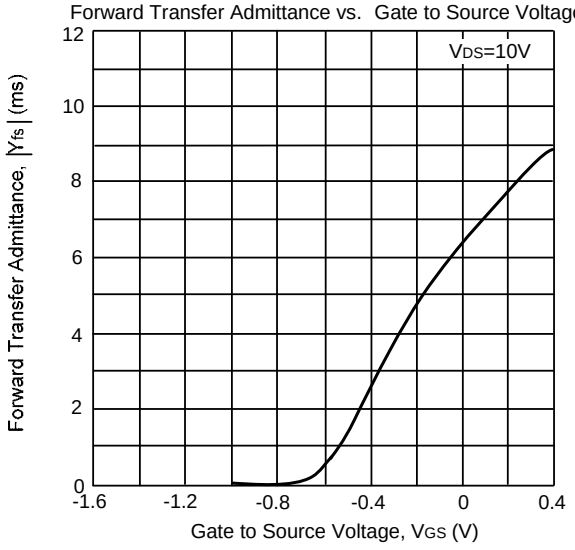
Drain Current vs. Drain Source Voltage



Drain Current vs. Gate to Source Voltage



Forward Transfer Admittance vs. Gate to Source Voltage



Forward Transfer Admittance vs. Drain Current